

| | Type | L # | Hits | Search Text | DBs |
|---|------|-----|------|--|--|
| 1 | BRS | L1 | 100 | min near tai.in. | US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B |
| 2 | BRS | L2 | 116 | wang near po.in. | US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B |
| 3 | BRS | L3 | 1571 | 438/3.ccls. | US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B |
| 4 | BRS | L4 | 2152 | ((mtj) or (magnetic near tunnel near junction)) | US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B |

| | Type | L # | Hits | Search Text | DBs |
|---|------|-----|------|--|--|
| 5 | BRS | L5 | 401 | ((mtj) or (magnetic near tunnel near junction)) near25 (wafer or substrate) | US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B |
| 6 | BRS | L6 | 167 | ((mtj) or (magnetic near tunnel near junction)) near5 (cell))near25 (wafer or substrate) | US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B |
| 7 | BRS | L7 | 167 | ((mtj) or (magnetic near tunnel near junction)) near5 (cell)) near25 (wafer or substrate) | US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B |
| 8 | BRS | L8 | 10 | 7 and (shiel\$3) | US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B |

| | Type | L # | Hits | Search Text | DBs |
|----|------|-----|------|---|--|
| 9 | BRS | L9 | 0 | ((mtj) or (magnetic near tunnel near junction)) near25 (wafer or substrate) near45 (shile\$3) | US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B |
| 10 | BRS | L10 | 27 | ((mtj) or (magnetic near tunnel near junction)) near25 (wafer or substrate) near45 (shiel\$3) | US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B |
| 11 | BRS | L11 | 209 | ((mtj) or (magnetic near tunnel near junction)) near25 (wafer or substrate) near45 (magnetic\$3) | US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B |
| 12 | BRS | L12 | 212 | ((mtj) or (magnetic near tunnel near junction)) near25 (wafer or substrate) near45 (magneti\$5) | US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B |

| | Type | L # | Hits | Search Text | DBs |
|----|------|-----|-------|---|--|
| 13 | BRS | L13 | 71944 | ((mtj) or (magnet\$5)) near25 (wafer or substrate) near45 (magnet\$5) | US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B |
| 14 | BRS | L14 | 71251 | ((mtj) or (magnet\$2)) near25 (wafer or substrate) near45 (magnet\$5) | US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B |
| 15 | BRS | L15 | 71251 | ((mtj) or (magnet\$2)) near25 ((wafer or substrate))) near45 (magnet\$5) | US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B |
| 16 | BRS | L16 | 96651 | ((mtj) or (magnet\$2)) near25 ((wafer or substrate))) | US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B |

| | Type | L # | Hits | Search Text | DBs |
|----|------|-----|-------|--|--|
| 17 | BRS | L17 | 65789 | ((mtj) or (magnet\$2)) near5 ((wafer or substrate))) | US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B |
| 18 | BRS | L18 | 96651 | ((mtj) or (magnet\$2)) near25 ((wafer or substrate))) | US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B |
| 19 | BRS | L19 | 118 | ((mtj) or (magnet\$2)) near (cell)) near25 ((wafer or substrate))) | US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B |
| 20 | BRS | L20 | 108 | ((magnetic near memory) near (cell)) near25 ((wafer or substrate)) | US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B |

| | Type | L # | Hits | Search Text | DBs |
|----|------|-----|------|--|--|
| 21 | BRS | L21 | 0 | ((magnetic-memory) near (cell)) near25 ((wafer or substrate)) | US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B |
| 22 | BRS | L22 | 23 | (magnetic\$3 near3 shield\$2) near35 (mtj) | US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B |
| 23 | BRS | L23 | 33 | (magnetic\$3 near3 shield\$2) near35 (magnetic near tunnel\$3) | US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B |

| | U | 1 | Document ID | Title |
|----|---|---|-------------------|--|
| 1 | | | US 20050059170 A1 | Magnetic random access memory designs with patterned and stabilized magnetic shields |
| 2 | | | US 20050059170 A1 | Magnetic random access memory designs with patterned and stabilized magnetic shields |
| 3 | | | US 20050045971 A1 | Magnetic memory with self-aligned magnetic keeper structure |
| 4 | | | US 20040174756 A1 | Magnetic memory device and magnetic substrate |
| 5 | | | US 20030210591 A1 | Magnetic memory device and magnetic substrate |
| 6 | | | US 20030156449 A1 | Thin film magnetic memory device having communication function, and distribution management system and manufacturing step management system each using thereof |
| 7 | | | US 20020145902 A1 | Magnetic memory device and magnetic substrate |
| 8 | | | US 6795339 B2 | Thin film magnetic memory device having communication function, and distribution management system and manufacturing step management system each using thereof |
| 9 | | | US 6741495 B2 | Magnetic memory device and magnetic substrate |
| 10 | | | US 6567299 B2 | Magnetic memory device and magnetic substrate |